

CMP10N80/CMB10N80/CMI10N80/CMF10N80

800V, 0.81Ω typ., 10A N-Channel MOSFET

General Description

These Power MOSFETs are produced using Cmos's proprietary, planar stripe, DMOS technology. These devices are well suited for high efficiency switch mode power supplies.

Features

- 100% avalanche tested
- Improved dv/dt capability
- RoHS Compliant

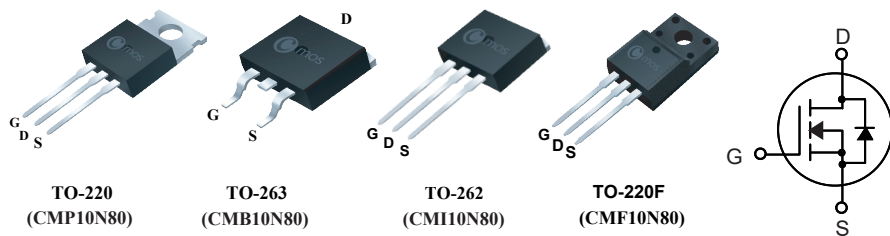
Product Summary

BVDSS	R _{DS(on)} max.	ID
800V	1Ω	10A

Applications

- Switch Mode Power Supply
- Uninterruptable Power Supply

TO-220/263/262/220F Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	220/263/262	220F	Units
V _{DS}	Drain-Source Voltage	800		V
V _{GS}	Gate-Source Voltage	±30		V
I _D @T _C =25°C	Continuous Drain Current	10	10*	A
I _D @T _C =100°C	Continuous Drain Current	6.3	6.3*	A
I _{DM}	Pulsed Drain Current	40	40*	A
EAS	Single Pulse Avalanche Energy (Note 1)	1500		mJ
P _D @T _C =25°C	Total Power Dissipation	240	60	W
T _{STG}	Storage Temperature Range	-55 to 150		°C
T _J	Operating Junction Temperature Range	150		°C

* Drain current limited by maximum junction temperature.

Thermal Data

Symbol	Parameter	220/263/262	220F	Unit
R _{θJA}	Thermal Resistance Junction-ambient Max.	62.5	62.5	°C/W
R _{θJC}	Thermal Resistance Junction-case Max.	0.52	2.08	°C/W

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Electrical Characteristics (T_J=25°C , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	800	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V , I _D =5A	---	0.81	1	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	3	---	5	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =800V , V _{GS} =0V	---	---	1	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±30V , V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =15V , I _D =10A	---	27	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	1.1	---	Ω
Q _g	Total Gate Charge	I _D = 10A	---	58	---	nC
Q _{gs}	Gate-Source Charge	V _{DS} =640V	---	21	---	
Q _{gd}	Gate-Drain Charge	V _{GS} = 10V	---	18	---	
T _{d(on)}	Turn-On Delay Time	V _{DS} =400V I _D = 10A R _G =25Ω	---	50	---	ns
T _r	Rise Time		---	130	---	
T _{d(off)}	Turn-Off Delay Time		---	90	---	
T _f	Fall Time		---	80	---	
C _{iss}	Input Capacitance	V _{DS} =25V , V _{GS} =0V , f=1MHz	---	2600	---	pF
C _{oss}	Output Capacitance		---	190	---	
C _{rss}	Reverse Transfer Capacitance		---	18	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _{GS} =V _{DS} =0V , Force Current	---	---	10	A
I _{SM}	Pulsed Source Current		---	---	40	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V , I _{SD} =10A , T _J =25°C	---	0.84	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} =0V	---	650	---	ns
Q _{rr}	Reverse Recovery Charge	I _F =10A , di/dt=100A/μs	---	10.9	---	uC

Note :

1.The EAS data shows Max. rating . The test condition is V_{DD}=80V , V_{GS}=10V , L=30mH , I_{AS} =10A.

This product has been designed and qualified for the consumer market.
Cmos assumes no liability for customers' product design or applications.
Cmos reserves the right to improve product design ,functions and reliability without notice.

Typical Characteristics

